

Abstract

The present invention relates to a method for modifying the electronic properties of a surface to analytical ends, such as SIMS or electron spectroscopy, characterised in that it comprises in situ deposition of pure neutral cesium (Cs^0), under ultra-high vacuum, said neutral cesium being enabled in the form of a collimated adjustable stream. The invention relates also to the special column designed for implementing the method and to the corresponding energy and/or mass analyser instrument.